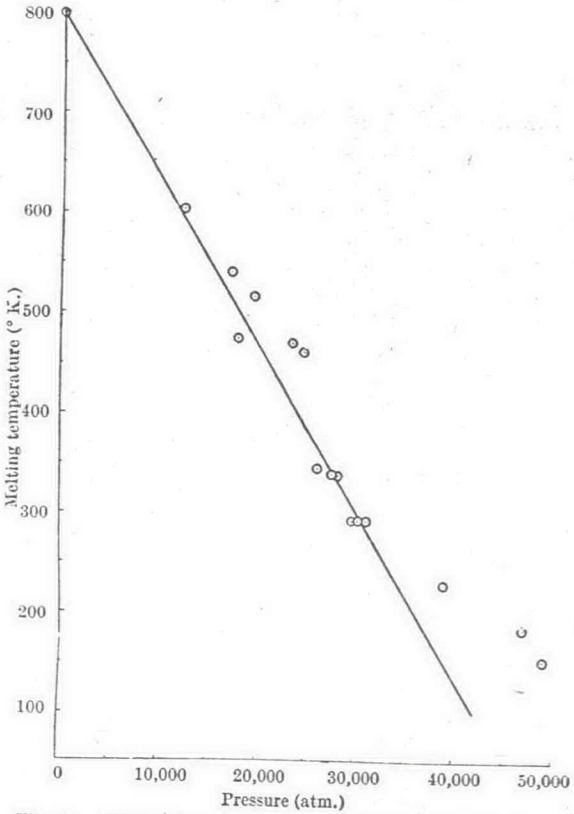

Fig. 2. Effect of pressure on the melting point of indium antimonide

tetrahedron had a side of $\frac{3}{4}$ in. and electrical connexions were made by the techniques described by Hall[3]. Cooling coils allowed the temperature to be lowered to 120° K. Pressure-versus-load calibration was made by measuring resistance changes in bismuth, thallium and barium specimens and using Bridgman's electrical data[4].

Fig. 1 shows typical behaviour of single-crystal specimens of indium antimonide at two temperatures. Initially, the resistance increases with pressure as found by Keyes, who showed that this effect comes mainly from a widening of the energy gap. In our room-temperature experiments, the resistance dropped sharply at a pressure of 30,000 atmospheres. This is attributed to melting, with a transition from semiconduction in the crystal to metallic conduction in